

## High speed switching series fifth generation

## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	$V_{CE}$	650	V
DC collector current, limited by $T_{vjmax}$ $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	$I_C$	80.0 53.5	A
Pulsed collector current, $t_p$ limited by $T_{vjmax}^{1)}$	$I_{Cpuls}$	150.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}^{1)}$	-	150.0	A
Diode forward current, limited by $T_{vjmax}$ $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	$I_F$	40.0 27.0	A
Diode pulsed current, $t_p$ limited by $T_{vjmax}^{1)}$	$I_{Fpuls}$	150.0	A
Gate-emitter voltage Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )	$V_{GE}$	$\pm 20$ $\pm 30$	V
Power dissipation $T_C = 25^{\circ}\text{C}$ Power dissipation $T_C = 100^{\circ}\text{C}$	$P_{tot}$	270.0 136.0	W
Operating junction temperature	$T_{vj}$	-40...+175	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^{\circ}\text{C}$
Soldering temperature, <sup>2)</sup> wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	$M$	0.6	Nm

## Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b><math>R_{th}</math> Characteristics</b>						
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.55	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		-	-	1.50	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> Package not recommended for surface mount applications

High speed switching series fifth generation

**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.20\text{mA}$	650	-	-	V
Collector-emitter saturation voltage	$V_{CESat}$	$V_{GE} = 15.0\text{V}, I_C = 50.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.66	2.10	V
			-	1.91	-	
			-	2.04	-	
Diode forward voltage	$V_F$	$V_{GE} = 0\text{V}, I_F = 25.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.54	1.80	V
			-	1.53	-	
			-	1.50	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.50\text{mA}, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	-	40	$\mu\text{A}$
			-	1000	-	
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE} = 20\text{V}, I_C = 50.0\text{A}$	-	62.0	-	S

**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	3050	-	pF
Output capacitance	$C_{oes}$		-	69	-	
Reverse transfer capacitance	$C_{res}$		-	11	-	
Gate charge	$Q_G$	$V_{CC} = 520\text{V}, I_C = 50.0\text{A},$ $V_{GE} = 15\text{V}$	-	116.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13.0	-	nH

**Switching Characteristic, Inductive Load**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

**IGBT Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$** 

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 25.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega,$ $L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ $L_{\sigma}, C_{\sigma}$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	21	-	ns
Rise time	$t_r$		-	12	-	ns
Turn-off delay time	$t_{d(off)}$		-	173	-	ns
Fall time	$t_f$		-	11	-	ns
Turn-on energy	$E_{on}$		-	0.45	-	mJ
Turn-off energy	$E_{off}$		-	0.16	-	mJ
Total switching energy	$E_{ts}$	-	0.61	-	mJ	